

# 2N7000G

## Small Signal MOSFET 200 mAmps, 60 Volts N-Channel TO-92

### Features

- AEC Qualified
- PPAP Capable
- This is a Pb-Free Device\*

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	60	Vdc
Drain-Gate Voltage ( $R_{GS} = 1.0 \text{ M}\Omega$ )	$V_{DGR}$	60	Vdc
Gate-Source Voltage	$V_{GS}$	$\pm 20$	Vdc
- Continuous	$V_{GSM}$	$\pm 40$	Vpk
- Non-repetitive ( $t_p \leq 50 \mu\text{s}$ )			
Drain Current	$I_D$	200	mAdc
- Continuous	$I_{DM}$	500	
- Pulsed			
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	350 2.8	mW mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	$T_L$	300	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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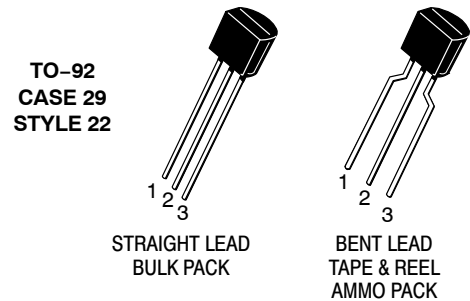
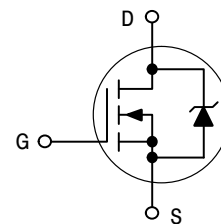
<http://onsemi.com>

**200 mAmps**

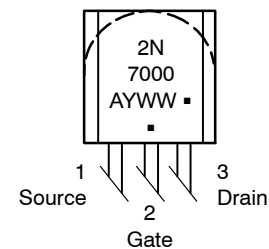
**60 Volts**

$R_{DS(on)} = 5 \Omega$

N-Channel



### MARKING DIAGRAM AND PIN ASSIGNMENT



- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# 2N7000G

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ( $V_{GS} = 0, I_D = 10 \mu\text{Adc}$ )	$V_{(BR)DSS}$	60	-	Vdc
Zero Gate Voltage Drain Current ( $V_{DS} = 48 \text{ Vdc}, V_{GS} = 0$ ) ( $V_{DS} = 48 \text{ Vdc}, V_{GS} = 0, T_J = 125^\circ\text{C}$ )	$I_{DSS}$	-	1.0	$\mu\text{Adc}$ mAdc
Gate-Body Leakage Current, Forward ( $V_{GSF} = 15 \text{ Vdc}, V_{DS} = 0$ )	$I_{GSSF}$	-	-10	nAdc

### ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc}$ )	$V_{GS(th)}$	0.8	3.0	Vdc
Static Drain-Source On-Resistance ( $V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc}$ ) ( $V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc}$ )	$r_{DS(on)}$	-	5.0 6.0	$\Omega$
Drain-Source On-Voltage ( $V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc}$ ) ( $V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc}$ )	$V_{DS(on)}$	-	2.5 0.45	Vdc
On-State Drain Current ( $V_{GS} = 4.5 \text{ Vdc}, V_{DS} = 10 \text{ Vdc}$ )	$I_{d(on)}$	75	-	mAdc
Forward Transconductance ( $V_{DS} = 10 \text{ Vdc}, I_D = 200 \text{ mAdc}$ )	$g_{fs}$	100	-	$\mu\text{mhos}$

### DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = 25 \text{ V}, V_{GS} = 0,$ $f = 1.0 \text{ MHz})$	$C_{iss}$	-	60	pF
Output Capacitance		$C_{oss}$	-	25	
Reverse Transfer Capacitance		$C_{rss}$	-	5.0	

### SWITCHING CHARACTERISTICS (Note 1)

Turn-On Delay Time	$(V_{DD} = 15 \text{ V}, I_D = 500 \text{ mA},$ $R_G = 25 \Omega, R_L = 30 \Omega, V_{gen} = 10 \text{ V})$	$t_{on}$	-	10	ns
Turn-Off Delay Time		$t_{off}$	-	10	

1. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

### ORDERING INFORMATION

Device	Package	Shipping†
2N7000G	TO-92 (Pb-Free)	1000 Units / Bulk
2N7000RLRAG	TO-92 (Pb-Free)	2000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# 2N7000G

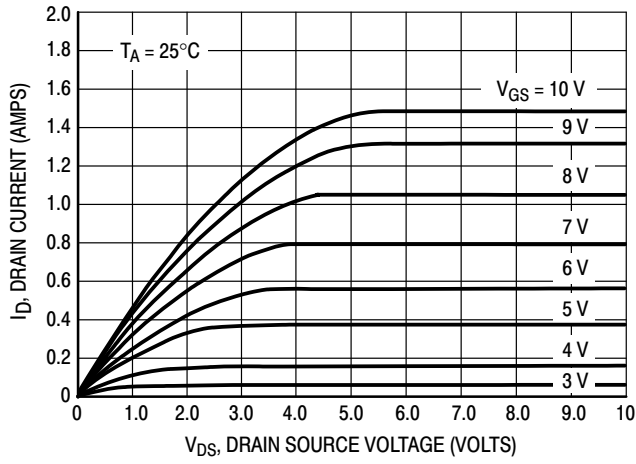


Figure 1. Ohmic Region

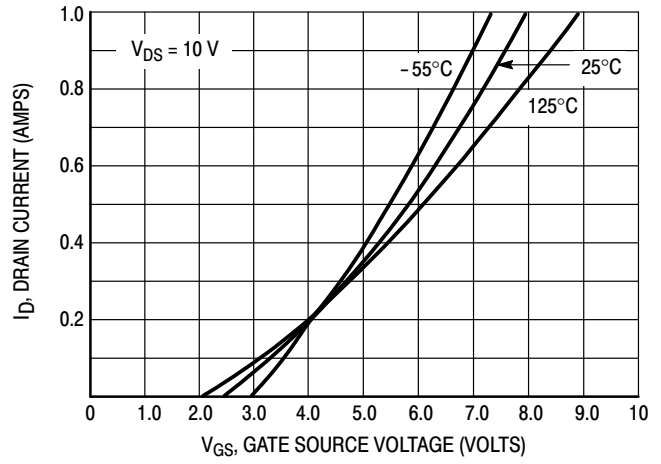


Figure 2. Transfer Characteristics

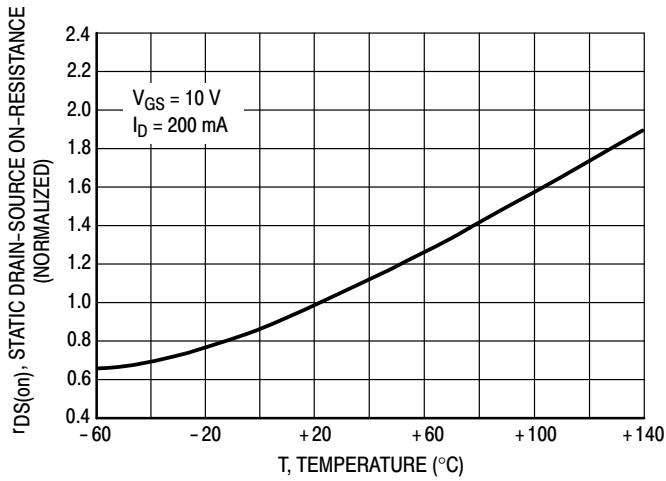


Figure 3. Temperature versus Static Drain-Source On-Resistance

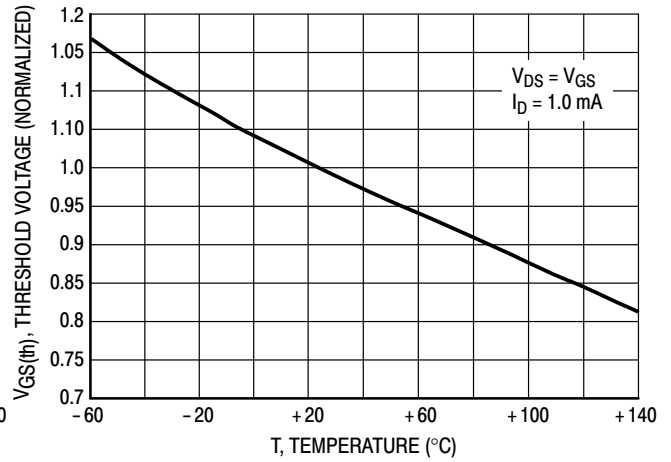
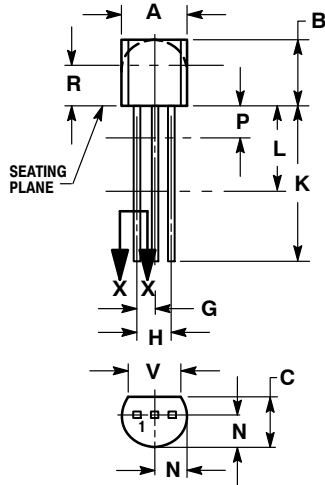


Figure 4. Temperature versus Gate Threshold Voltage

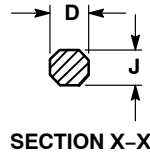
# 2N700G

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AM



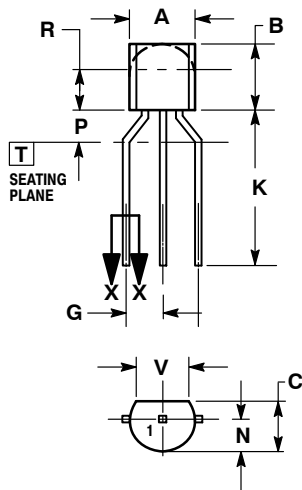
STRAIGHT LEAD  
BULK PACK



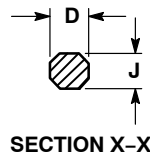
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 22:

1. SOURCE
2. GATE
3. DRAIN

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